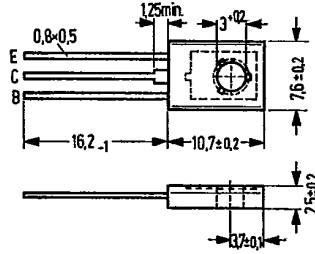


BF 470 and BF 472 are epitaxial PNP silicon planar transistors in TO 126 plastic package (12 A 3 DIN 41 869, sheet 4). The collector is conductively connected to the metallic mounting area of the transistor. With the complementary types BF 469 and BF 471 these transistors are particularly suitable for use in video B output stages of TV receivers.

Type	Ordering code
BF 470	Q62702-F498
BF 472	Q62702-F506
Spring washer A 3 DIN 137	Q62902-B63
Mica washer	Q62902-B62



Approx. weight 0.5 g Dimensions in mm

Maximum ratings

	BF 470	BF 472	
Collector-base voltage	-V _{CBO} 250	300	V
Collector-emitter voltage	-V _{CEO} 250	-	V
Collector-emitter voltage	-V _{CER} -	300	V
Emitter-base voltage	-V _{EBO} 5	5	V
Collector current	-I _C 30	30	mA
Collector peak current	-I _{CM} 100	100	mA
Junction temperature	T _j 150	150	°C
Storage temperature range	T _{stg} -65 to +150	-65 to +150	°C
Total power dissipation (T _{case} ≤ 110°C)	P _{tot} 2	2	W

Thermal resistance

Junction to ambient air ¹⁾	R _{thJA} ≤ 100	≤ 100	K/W
Junction to case	R _{thJC} ≤ 20	≤ 20	K/W

1) For fixing the transistors with max. 4 mm long leads on PCBs with a 10 mm² large copper area for the collector terminal.

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Static characteristics ($T_{amb} = 25^{\circ}\text{C}$)

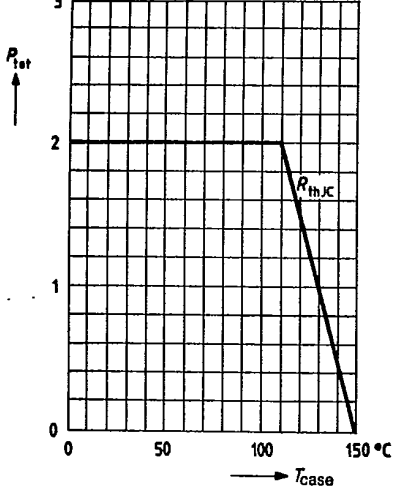
		BF 470	BF 472	
Collector-base breakdown voltage ($-I_C = 10 \mu\text{A}$)	$-V_{(BR)CBO}$	>250	>300	V
Collector-emitter breakdown voltage ($-I_C = 1 \mu\text{A}$)	$-V_{(BR)CEO}$	>250	-	V
Collector-emitter breakdown voltage ($R_{BE} = 2.7 \text{ k}\Omega$)	$-V_{(BR)CER}$	-	>300	V
Emitter-base breakdown voltage ($I_E = 10 \mu\text{A}$)	$-V_{(BR)EBO}$	>5	>5	V
Collector cutoff current ($-V_{CE} = 200 \text{ V}; R_{BE} = 2.7 \text{ k}\Omega; T_{amb} = 150^{\circ}\text{C}$)	$-I_{CER}$	≤ 10	≤ 10	μA
Collector cutoff current ($-V_{CB} = 200 \text{ V}$)	$-I_{CBO}$	≤ 10	≤ 10	nA
Emitter cutoff current ($-V_{EB} = 5 \text{ V}$)	$-I_{EBO}$	≤ 10	≤ 10	μA
Collector-emitter saturation voltage ($-I_C = 25 \text{ mA}; T_J = 150^{\circ}\text{C}$)	$-V_{CEsat RF}$	20	-	V
($-I_C = 25 \text{ mA}; T_{amb} = 150^{\circ}\text{C}$)		-	20	V
DC current gain ($-I_C = 25 \text{ mA}; -V_{CE} = 20 \text{ V}$)	h_{FE}	≥ 50	≥ 40	-

Dynamic characteristics ($T_{amb} = 25^{\circ}\text{C}$)

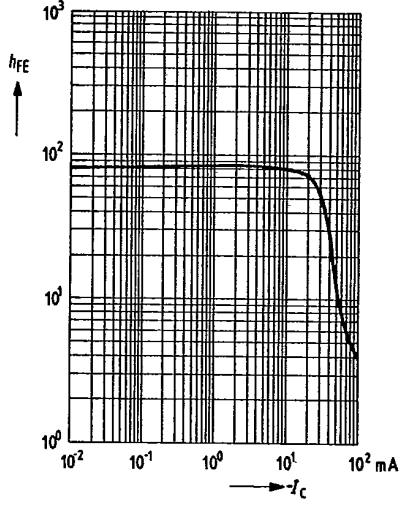
Transition frequency ($V_{CE} = 10 \text{ V}; -I_C = 10 \text{ mA}$)	f_T	≥ 60	≥ 60	MHz
Reverse transfer capacitance ($-V_{CB} = 30 \text{ V}$)	$-C_{12e}$	≤ 1.8	≤ 1.8	pF
Feedback time constant ($-V_{CB} = 20 \text{ V}; I_E = 10 \text{ mA}; f = 10.7 \text{ MHz}$)	$r_{bb'} C_{b'c}$	≤ 90	≤ 90	ps

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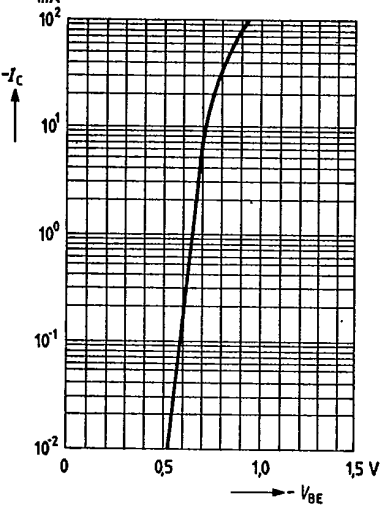
Total perm. power dissipation versus temperature
 $P_{tot} = f(T_{case})$



DC current gain $h_{FE} = f(I_C)$
 $-V_{CE} = 10\text{ V}; T_{case} = 25^\circ\text{C}$



Collector current $I_C = f(V_{BE})$
 $-V_{CE} = 10\text{ V}; T_{case} = 25^\circ\text{C}$



Transition frequency $f_T = f(I_C)$
 $-V_{CE} = 10\text{ V}; T_{case} = 25^\circ\text{C}$

